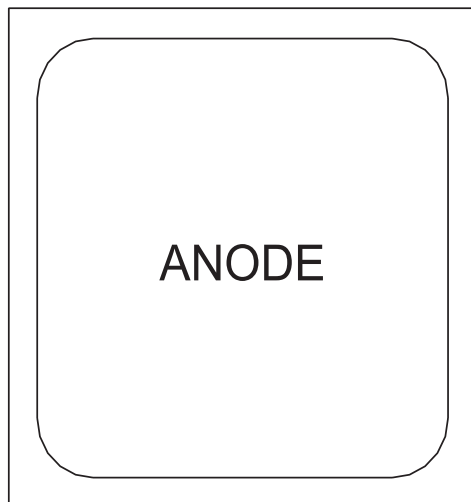


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	10.4 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

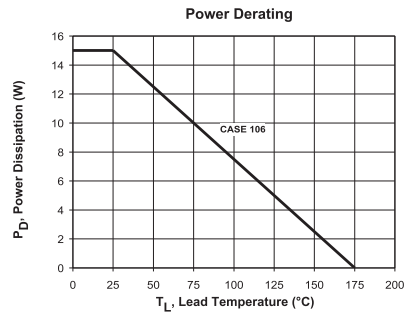
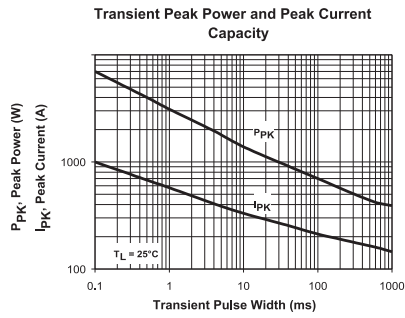
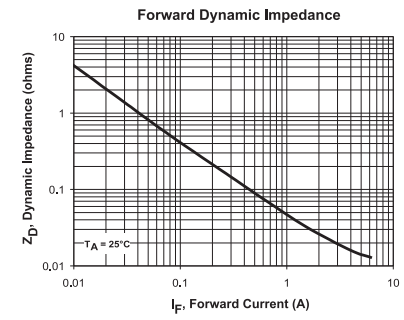
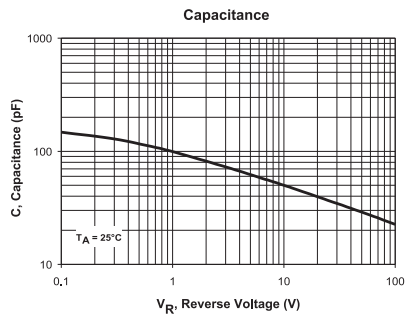
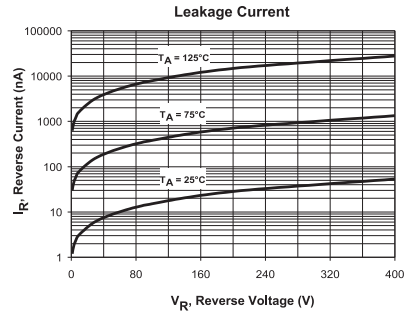
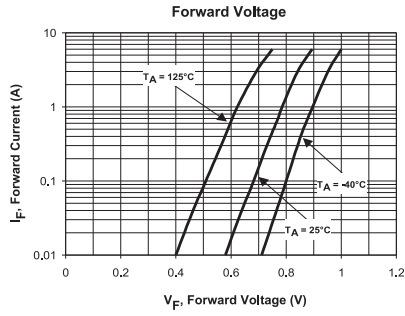
1,170

PRINCIPAL DEVICE TYPES

CR6A2GPP Series

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R2 (16-September 2003)



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